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(71) Applicant *(for all designated States except US)*: **MICRON TECHNOLOGY, INC.** [US/US]; 8000 South Federal Way, P.O. Box 6, Boise, ID 83716 (US).

(72) Inventors: **EPPICH, Denise, M.**; 3905 South Suntree Way, Boise, ID 83706 (US). **WEIMER, Ronald, A.**; 1696 E. Victory Road, Boise, ID 83706 (US).

(74) Agents: **LATWESEN, David, G.** et al.; Wells St. John P.S., 601 West First Avenue, Suite 1300, Spokane, WA 99201 (US).

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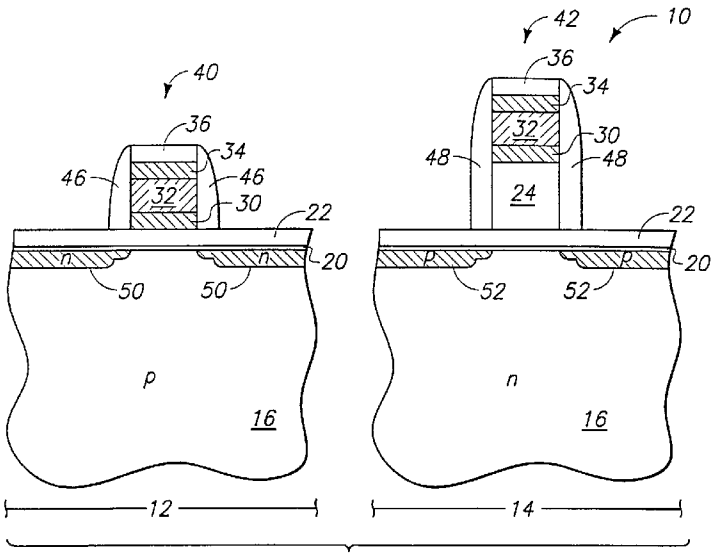
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(54) Title: SEMICONDUCTOR MOS, CMOS DEVICES AND CAPACITORS AND METHOD OF MANUFACTURING THE SAME



(57) Abstract: The invention includes methods of forming circuit devices. A metal-containing material comprising a thickness of no more than 20Å (or alternatively comprising a thickness resulting from no more than 70 ALD cycles) is formed between conductively-doped silicon and a dielectric layer. The conductively-doped silicon can be n-type silicon and the dielectric layer can be a high-k dielectric material. The metal-containing material can be formed directly on the dielectric layer, and the conductively-doped silicon can be formed directly on the metal-containing material. The circuit device can be a capacitor construction or a transistor construction. If the circuit device is a transistor construction, such can be incorporated into a CMOS assembly. Various devices of the present invention can be incorporated into memory constructions, and can be incorporated into electronic systems.

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